

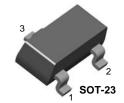
June 2007

# **BSR18B**

# **PNP General Purpose Amplifier**

This device is designed as a general purpose amplifier and switch.

Sourced from Process 23.



1. Base 2. Emitter 3. Collector



# **Absolute Maximum Ratings** ${}^{\star}T_a = 25^{\circ}C$ unless otherwise noted

Symbol	Parameter	Value	Units
V <sub>CBO</sub>	Collector-Base Voltage	40	V
V <sub>CEO</sub>	Collector-Emitter Voltage	40	V
$V_{EBO}$	Emitter-Base Voltage	5.0	V
I <sub>C</sub>	Collector Current (DC)	200	mA
$T_{J,}T_{STG}$	Junction Temperature, Storage Temperature	-55 ~ <b>+</b> 150	°C

<sup>\*</sup> These ratings are limiting values above which the serviceability of any semiconductor device may be impaired.

#### NOTES

- 1) These ratings are based on a maximum junction temperature of 150 degrees C.
- 2) These are steady state limits. The factory should be consulted on applications involving pulsed or low duty cycle operations.

## Thermal Characteristics \* T<sub>a</sub> = 25°C unless otherwise noted

Symbol	Characteristic	Max	Units
P <sub>D</sub>	Total Device Dissipation	230	mW
	Derate above 25°C	1.84	mW/°C
R ⊕ JA	Thermal Resistance, Junction to Ambient	550	°C/W

<sup>\*</sup>Device mounted on FR-4 PCB 1.6" X 1.6" X 0.06".

## Electrical Characteristics \* Ta = 25°C unless otherwise noted

Symbol	Parameter	Test Condition	MIN	MAX	Units
Off Charac	teristics				
V <sub>(BR)CEO</sub>	Collector-Emitter Breakdown Voltage	Ic = 1.0 mA, I <sub>B</sub> = 0	40		V
V <sub>(BR)</sub> CBO	Collector-Base Breakdown Voltage	Ic = 10 μA, Iε = 0	40		V
V <sub>(BR)EBO</sub>	Emitter-Base Breakdown Voltage	Iε = 10 μA, Ic = 0	5.0		V
Ісво	Collector-Cutoff Current	Vcb = 30 V		50	nA
<b>І</b> ЕВО	Emitter-Cutoff Current	Vce = 30 V, Veb = 3.0 V		50	nA

### **On Characteristics**

hfE	DC Current Gain	$\begin{tabular}{lc} Ic = 0.1 & mA, \ VcE = 1.0 \ V \\ Ic = 1.0 & mA, \ VcE = 1.0 \ V \\ Ic = 10 & mA, \ VcE = 1.0 \ V \\ Ic = 50 & mA, \ VcE = 1.0 \ V \\ Ic = 100 & mA$	60 80 110 60 30	220	
VcE(sat)	Collector-Emitter Saturation Voltage *	Ic = 10 mA, I <sub>B</sub> = 1.0 mA Ic = 50 mA, I <sub>B</sub> = 5.0 mA		0.25 0.4	V V
V <sub>BE</sub> (sat)	Emitter-Base Breakdown Voltage *	Ic = 10 mA, I <sub>B</sub> = 1.0 mA Ic = 50 mA, I <sub>B</sub> = 5.0 mA	0.65	0.85 0.95	V V

## **Small Signal Characteristics**

Ccb	Collector-Base Capacitance	$V_{CB} = 5.0 \text{ V}, I_E = 0, f = 100 \text{ kHz}$	4.5	pF
Ceb	Emitter-Base Capacitance	$V_{EB} = 0.5 \text{ V}, I_{C} = 0, f = 100 \text{ kHz}$	10	pF

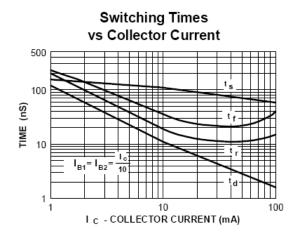
## **Switching Characteristics**

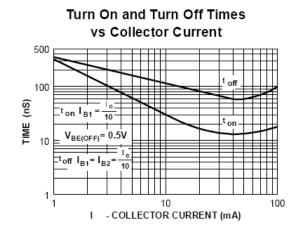
td	Delay Time	Ic = 10 mA, I <sub>B1</sub> = 1.0 mA, V <sub>cc</sub> = 3.0 V	35	ns
tr	Rise Time		35	pF
ts	Storage Time	Ic = 10 mA, IBon = IBoff = 1.0 mA	225	ns
tf	Fall Time	Vcc= 3.0 V	75	ns

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NOTE: All voltages (V) and currents (A) are negative polarity for PNP transistors.

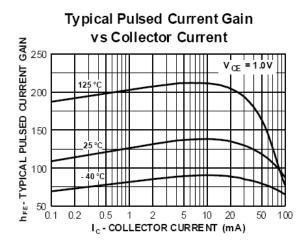
## **Typical Performance Characteristics**

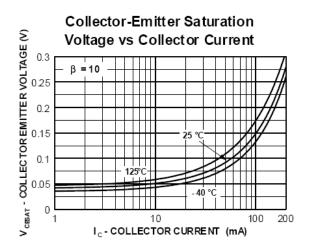


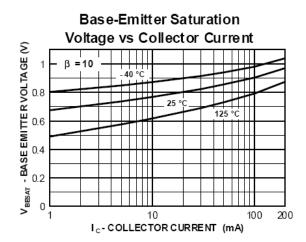


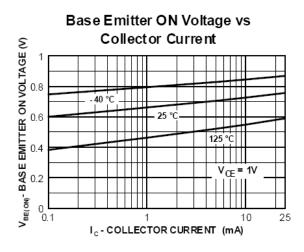
<sup>\*</sup> Pulse Test: Pulse Width $\leq$ 300 $\mu$ s, Duty Cycle $\leq$ 2%

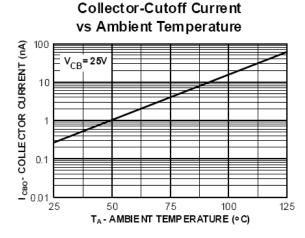
## **Typical Performance Characteristics (continued)**

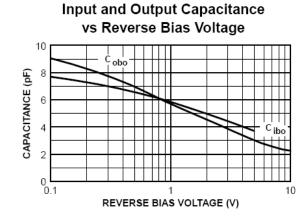












Common-Base Open Circuit





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